Thyristor Diode Modules

Liujing rectifier co., Ltd.

V_{RSM}	V_{RRM} V_{DRM}	I_{TRMS} =125A(maximum value for continous operation)		
V	V	I_{TAV} =70A(sin.180; Tc=85℃)		
900	800	SKKT 72/08E	SKKT 72B08E	SKKH 72/08E
1300	1200	SKKT 72/12E	SKKT 72B12E	SKKH 72/12E
1500	1400	SKKT 72/14E	SKKT 72B14E	SKKH 72/14E
1700	1600	SKKT 72/16E	SKKT 72B16E	SKKH 72/16E
1900	1800	SKKT 72/16E	SKKT 72B16E	SKKH 72/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; Tc = 85(100)℃;	70 (50)	A
I_D	P3/180 ; Ta = 45℃; B2 / B6	62 / 75	A
	P3/180F; Ta = 35℃; B2 / B6	115 / 145	A
I_{RMS}	P3/180F; Ta = 35℃; W1 / W3	155 / 3 * 115	A
I_{TSM}	T_{vj} = 25℃; 10ms	1600	A
	T_{vj} = 125℃; 10ms	1450	A
i^2t	T_{vj} = 25℃; 8，3 ...10ms	13000	A^2S
	T_{vj} = 125℃; 8，3 ...10ms	10500	A^2S
V_T	T_{vj} = 25℃; I_T=216A	max.1.9	V
$V_{T(TO)}$	T_{vj} = 125℃	max.0.9	V
r_T	T_{vj} = 125℃	max.3.5	mΩ
I_{DD};I_{RD}	T_{vj} = 125℃; V_{RD}=V_{RRM} ; V_{DD}=V_{DRM}	max.20	mA
t_{gd}	T_{vj} = 25℃; I_G = 1A; di$_G$/dt = A/µs	1	µs
t_{gr}	V_D = 0.67*V_{DRM}	1	µs
$(di/dt)_{cr}$	T_{vj} = 125℃	max.150	A/µs
$(dv/dt)_{cr}$	T_{vj} = 125℃	max.1000	V/µs
t_q	T_{vj} = 125℃	250	µs
I_H	T_{vj} = 25℃ ; typ./max	150/250	mA
I_L	T_{vj} = 25℃ ; RG = 33Ω ; typ./max	300/600	mA
V_{GT}	T_{vj} = 25℃ ; d.c.	min. 3	V
I_{GT}	T_{vj} = 25℃ ; d.c.	min. 150	mA
V_{GD}	T_{vj} = 125℃ ; d.c.	max. 0.25	V
I_{GD}	T_{vj} = 125 ℃ ; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor/per module	0.35 / 0.18	K/W
$R_{th(j-c)}$	sin. 180; per thyristor/per module	0.37 / 0.19	K/W
$R_{th(j-c)}$	rec. 120; per thyristor/per module	0.39 / 0.2	K/W
$R_{th(j-c)}$	per thyristor/per module	0.2 / 0.1	K/W
T_{vj}		- 40...+ 125	℃
T_{stg}		- 40...+ 125	℃
V_{isol}	a. c. 50Hz; r.m.s. ; 1s/1min	3600/3000	V~
M_s	to heatsink	5 ± 15%[1])	Nm
M_t	to terminal	3 ± 15%	Nm
a		5 * 9.81	m/s^2
m	approx.		g
Case	SKKH	LJ1	

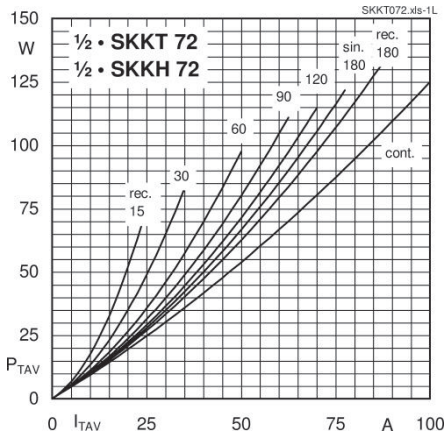


Fig. 1L Power dissipation per thyristor vs. on-state current

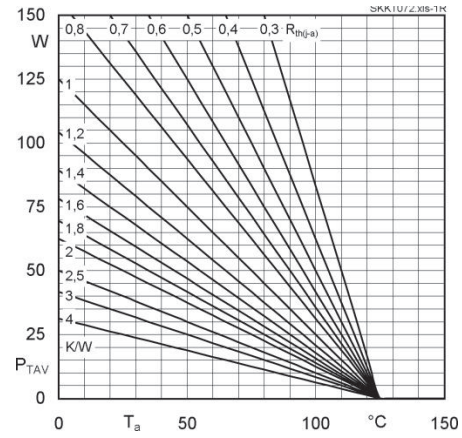


Fig. 1R Power dissipation per thyristor vs. ambient temp.

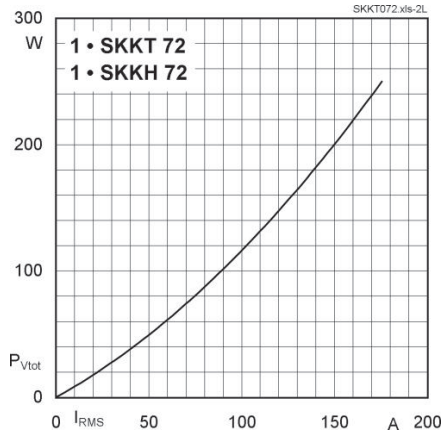


Fig. 2L Power dissipation per module vs. rms current

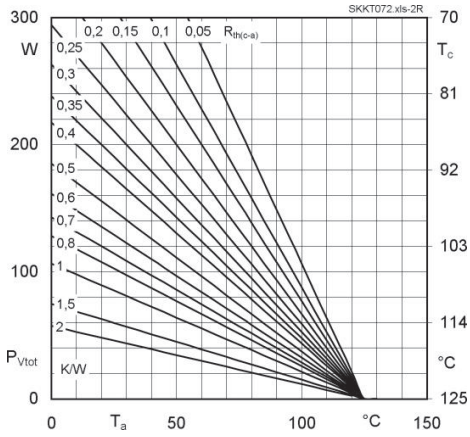


Fig. 2R Power dissipation per module vs. case temp.

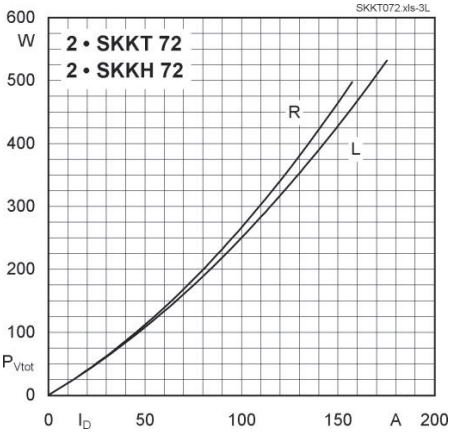


Fig. 3L Power dissipation of two modules vs. direct current

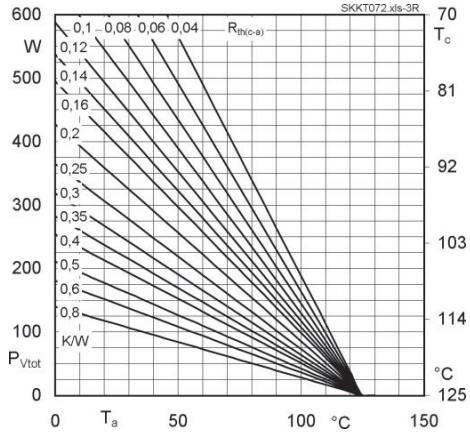


Fig. 3R Power dissipation of two modules vs. case temp.

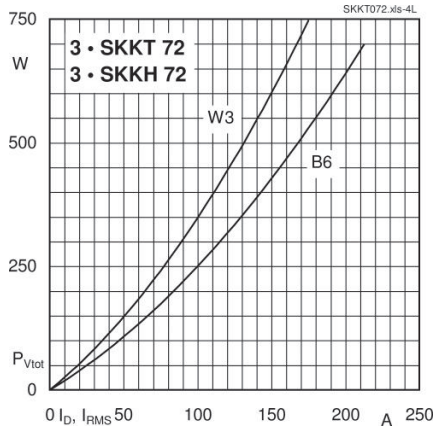


Fig. 4L Power dissipation of three modules vs. direct and rms current

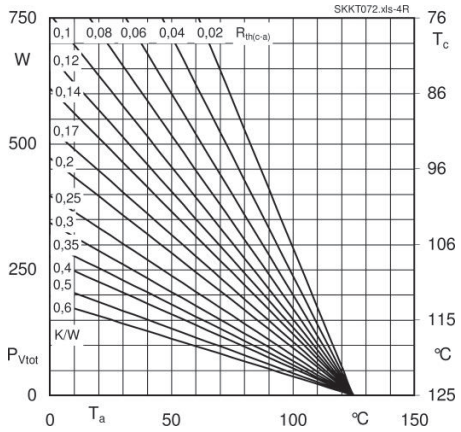


Fig. 4R Power dissipation of three modules vs. case temp.

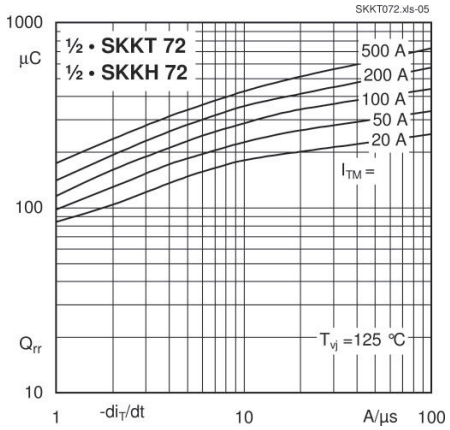


Fig. 5 Recovered charge vs. current decrease

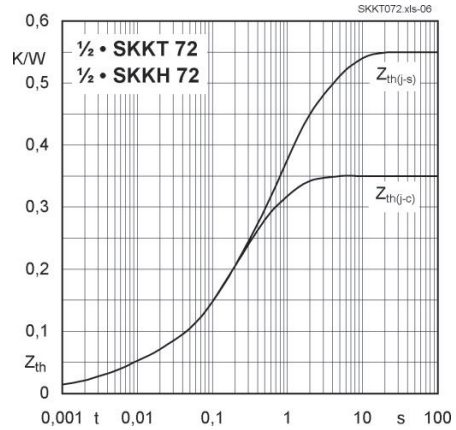


Fig. 6 Transient thermal impedance vs. time

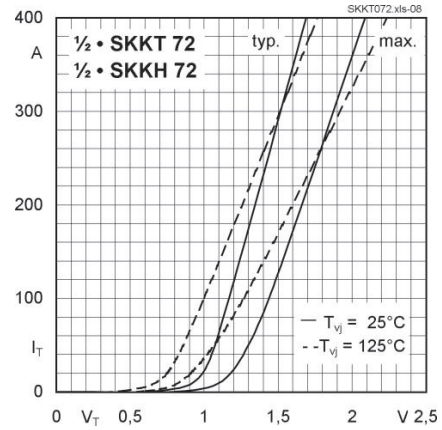


Fig. 7 On-state characteristics

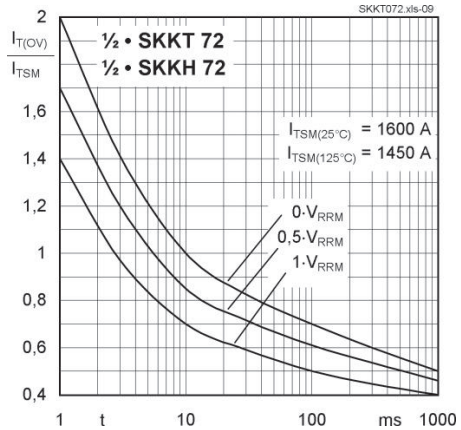
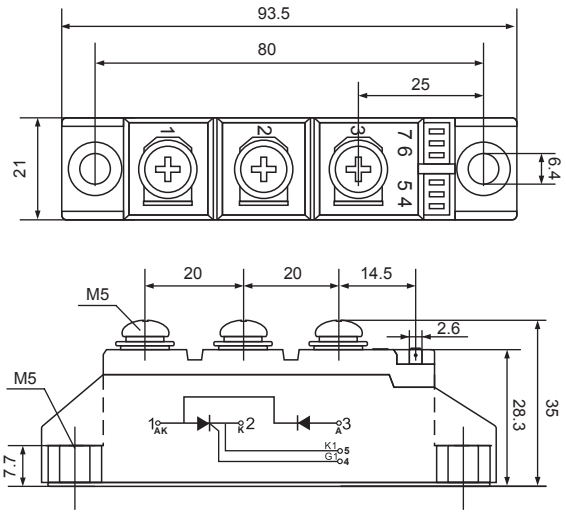


Fig. 8 Surge overload current vs. time



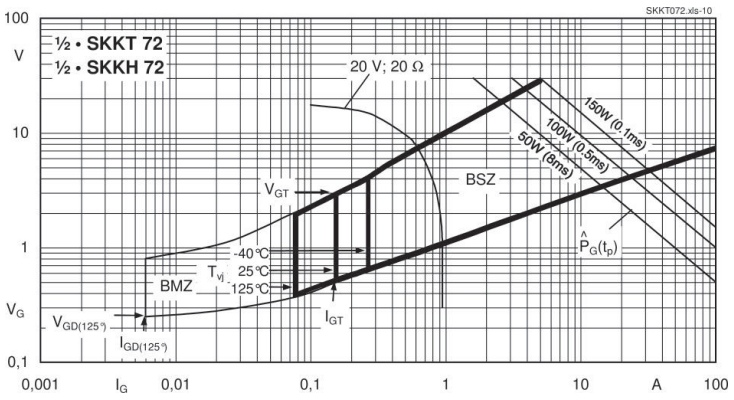


Fig. 9 Gate trigger characteristics

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